

TP44200SG-DPT-EVB

Switching Test Evaluation Board

For

Tagore Technology's Superior GaN FET
(TP44200SG)

User Manual

Rev-1.1

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powergan@tagoretech.com

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1 Introduction

This Double Pulse Test (DPT) Evaluation Board (EVB) TP44200SG-DPT-EVB provides users the platform to evaluate the switching behavior of Tagore Technology’s “Enhancement Mode High Electron Mobility GaN Transistors (E-HEMTs) with ESD protection” parts. This document should be used as a user guide only by professionals with adequate technical knowledge. TP44200SG-DPT-EVB can be used to measure switching energy loss, turn-on, and turn-off time.

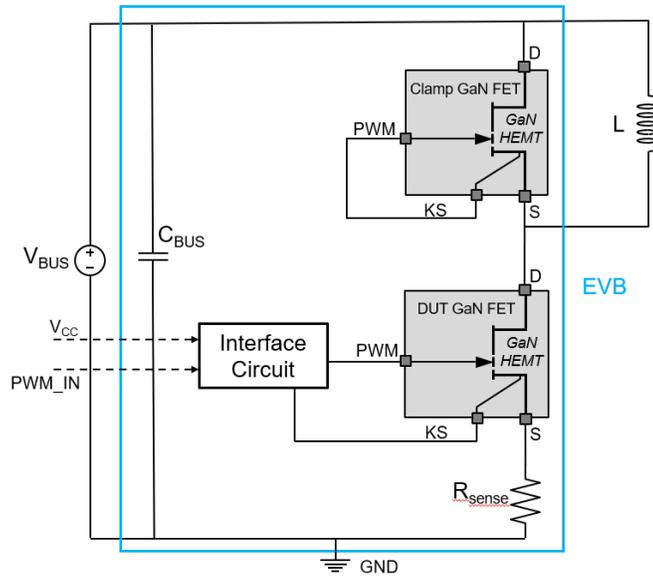


Figure 1-1: Simplified Circuit Diagram of Double Pulse Test Setup.

Figure 1-1 shows a simplified schematic of the Double Pulse Test setup using the TP44200SG-DPT-EVB. Tagore Technology’s E-HEMT part, TP44200SG is shown as the Device Under Test (DUT). The test setup is fed from a HV DC power source whose voltage is denoted by V_{BUS} . An inductor of inductance L is connected between the drain of the DUT and the positive terminal of V_{BUS} . This inductor is not part of the EVB. When DUT turns on, current will flow from V_{BUS} to the DUT through the inductor. Another TP44200SG acts as the clamp diode. It helps freewheel the inductor current whenever the DUT turns off. The interface circuit provides isolation and adjusts the pulsed control signal (PWM_IN) for the gate, as per the requirement of the DUT. A set of DC bus capacitors (combination of Al-electrolytic and ceramic capacitors, lumped as C_{BUS}) is connected between the input terminals of V_{BUS} to limit voltage fluctuations. Control signal PWM_IN, having two pulses (as shown in Figure 1-2), is fed to the DUT to turn it ON and OFF. When DUT turns ON, the inductor current will flow through the DUT.

Pulse #1 of duration t_1 will determine the switching test current I_{SW} of the DUT as the inductor current I_L builds up from 0 to I_{SW} during this pulse. It remains almost constant at I_{SW} during the period t_2 in between two pulses. It again starts increasing during the Pulse #2 with a duration of t_3 . The Turn-on and Turn-Off switching transitions can be captured in DSO during the rising edge of PWM pulse #2, and falling edge of PWM pulse #1, respectively.

The rise in inductor current ΔI_L during pulse duration of t_n is given by the following equation:

$$\Delta I_L = \frac{V_{BUS}}{L} \cdot t_n$$

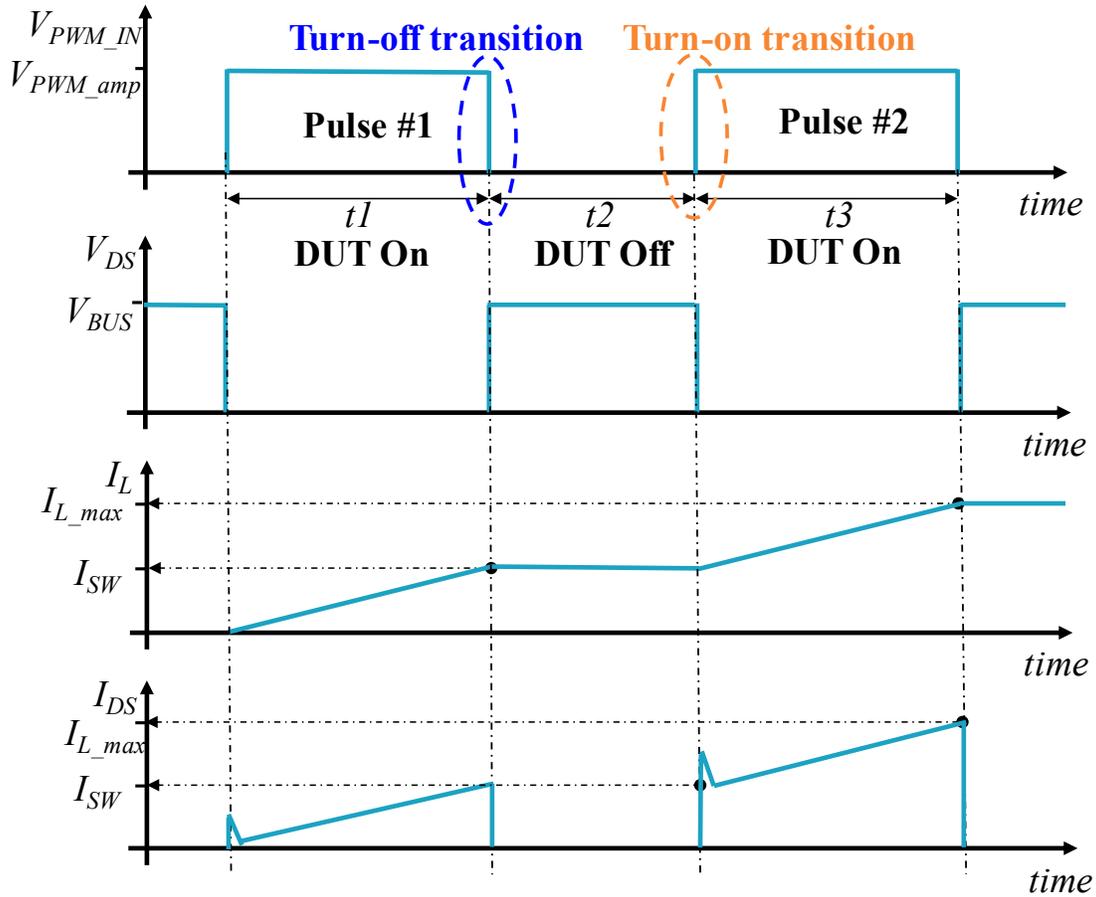


Figure 1-2: Timing Diagram of Double Pulse Test.

Users should be careful while selecting the pulse durations $t1$ and $t3$ as these time periods will determine the DUT currents for any given V_{BUS} and L . It is recommended that before performing the actual DPT, the user should calculate the estimated values of $t1$, $t2$ and $t3$ based on the required current settings and V_{BUS} and L values. The duration of $t2$ should not be too long to ensure that the inductor current stays nearly constant during this freewheeling period. Typically, $t2$ should be less than $1 \mu s$. The maximum Inductor and DUT current I_{L_max} should be within the recommended maximum pulsed current value mentioned in the datasheet of the DUT. The inductor should be chosen appropriately so that it can carry this current without getting saturated.

2 Physical Details Of EVB

Photographs of both the top and bottom sides of the TP44200SG-DPT-EVB are shown in Figure 2-1 with key components and test points identified.

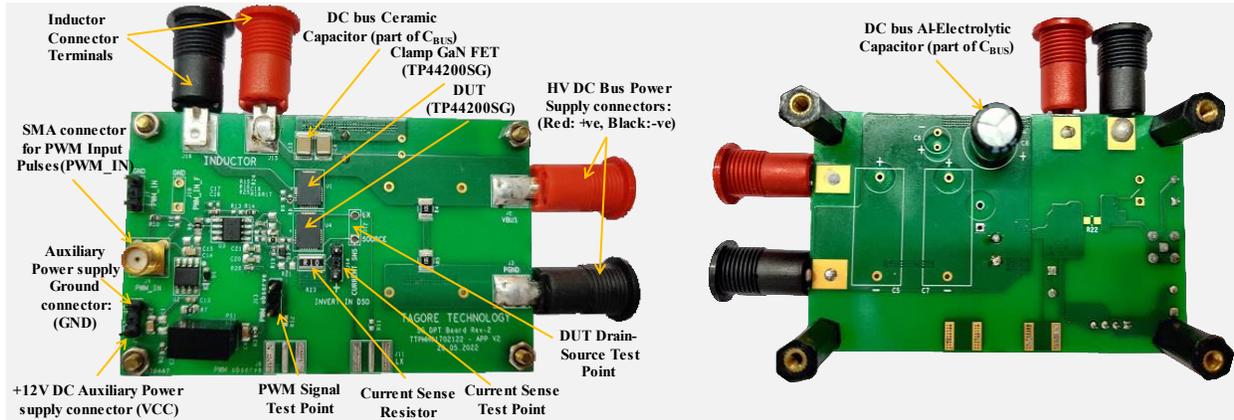


Figure 2-1: Photographs of TP44200SG-DPT-EVB with key components and test points identified. Top View (left); Bottom View (right).

2.1 Dimension Measurements

Table 2-1 : Mechanical Dimensions

Mechanical Dimensions	Value	Unit
Length of EVB PCB	86.16	mm
Width of EVB PCB	55	mm
Thickness of PCB	1.6	mm
Height of tallest component on Top Side	12	mm
Height of tallest component on Bottom Side	21	mm

2.2 Technical Data

Table 2-2 : Electrical Parameter Ratings

Parameter	Symbol	Value	Unit	Comments
High Voltage (DC) Input	VBUS	400	V	Maximum
Auxiliary DC Power Supply Voltage	VCC_IN	12	V	0.2 A min. current rating
Amplitude voltage of input PWM pulse	PWM_IN	5	V	Maximum
		4	V	Minimum
Maximum Drain-Source current of DUT	I _{L_max}	**	A	Please check datasheet of DUT

**Check the latest datasheet to get the Maximum Drain-Source current of DUT. Recommended value should not be exceeded.

3 Operating Procedure

3.1 List Of Instruments and Hardware Items Required

For DPT the following list of instruments and hardware items are required:

- TP44200SG-DPT-EVB eval board
- Inductor (preferably with shielding and low parasitic capacitance for cleaner waveforms)
- Controllable PWM signal source (preferably a DSP with 5V amplitude output)
- Power Sources:
 - Auxiliary power source: 12 V DC, 200mA (min)
 - High Voltage Power source: 400V DC (max)
- Observation Instruments:
 - Digital Storage Oscilloscope (*abr.* DSO) (Preferably with 4 Channels, BW \geq 300 MHz)
 - High Voltage Probe (min. 500 V and preferably with spring ground lead) compatible with the DSO
 - Low Voltage Probe/Active Probe compatible with the DSO
 - Current Probe for observing Inductor current (optional)
- Wires and cables for making electrical connections.

3.2 Operating Procedure Steps

- **Step 1:** Connect an inductor in between the connectors J15 and J16 on the TP44200SG-DPT-EVB. Typically, the recommended value of the inductor is in the range of 50 μ H to 100 μ H.
- **Step 2:** Connect output from a controllable PWM signal source to either SMA connector J9 or header J7.
- **Step 3:** Connect output terminals of an Auxiliary 12 V DC source to the 2-pin header connector J1, to supply power to the interface circuit.
- **Step 4:** To observe the PWM input signal going into the DUT, connect a low-voltage probe from DSO to header connector J13.
- **Step 5:** To observe the Drain-Source voltage signal of the DUT, connect a high-voltage probe from DSO, at connector J12. More details on the probe connection are given in Section 3.3.
- **Step 6:** To observe the Drain-Source current signal of the DUT, connect an Active probe or a low voltage probe from DSO, at connector J14 and invert the signal in DSO. However, this step can be skipped if available DSO channels are limited. More details on the probe connection are given in Section 3.4.
- **Step 7: (Optional)** Connect current probe to any lead wire of the inductor.
- **Step 8:** Turn on the 12 V DC source output with a current limit of 200mA, and then turn on the HV DC source output. It is recommended to first check the test setup at low voltage (preferably less than 30 V). Then release a test pulse signal from the PWM signal generator and observe the waveforms in DSO.
- **Step 9:** If the test setup is ok, then gradually increase the HV DC source output to the desired value up to 400 V. Adjust the PWM pulse widths to get the desired DUT current (limit the peak current to the recommended values as per datasheet of the DUT), and then release the Double Pulse signal from PWM signal generator.

Note that the EVB is designed for the Double Pulse Test only. Make sure there is at least 100 ms rest period (no current period) available between two consecutive sets of pulses (in case of continuous operation) to provide sufficient cooling time for the DUT as there is no heatsink attached to it.

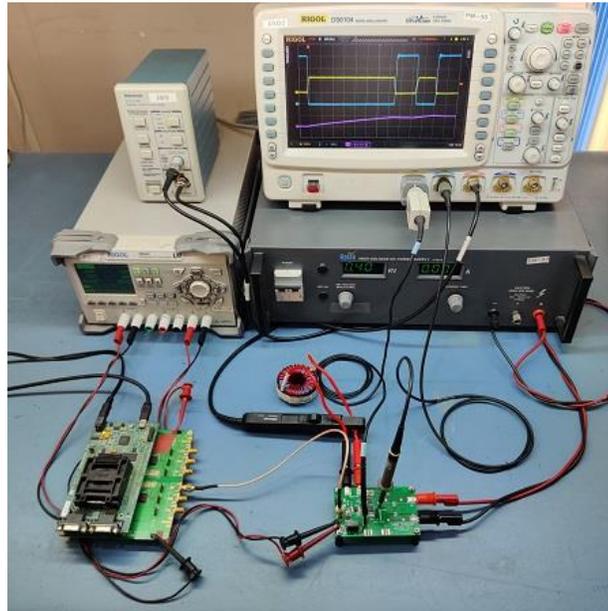


Figure 3-1: Typical Lab Test Setup for DPT.

3.3 Recommended Probe Connection to Observe DUT Drain-Source Voltage

For observing Drain-Source voltage waveform of DUT, the user can connect a voltage probe across the test point J12 with ground lead connected to the “Source” terminal and probe tip connected to the terminal marked as “LX”.

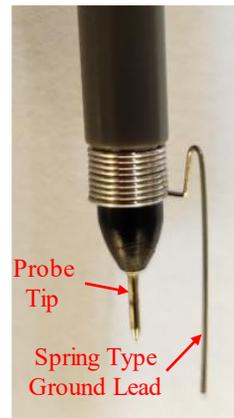


Figure 3-2: Recommended HV probe connection for observing Drain-Source voltage (Left image). Voltage probe with Spring Type Ground lead identified (Right image).

It is recommended to use spring lead for the ground connection of the voltage probe as shown in Figure 3-2. This will help in reducing noise in the waveform observed through DSO. The user should check and ensure that the voltage rating of the probe is higher than the applied HV DC bus voltage while testing the EVB.

3.4 Recommended Probe Connection to Observe DUT Drain-Source Current

For observing Drain-Source current waveform of DUT, the user can probe the voltage across the 0.1Ω current sense resistor on the EVB through the test point J14. The tip of the voltage probe should be inserted in the terminal marked by a (+) sign. This will ensure that the voltage probe connection is referred to the ‘Source’ node of the DUT. Invert this voltage probe signal in DSO to observe current flow from Drain to Source in correct polarity. It is recommended to use an Active probe as shown in Figure 3-3. This will help in reducing noise in the waveform observed through DSO. Alternatively, a low-voltage probe with spring-type ground lead can also be used to observe current waveform with better noise immunity.

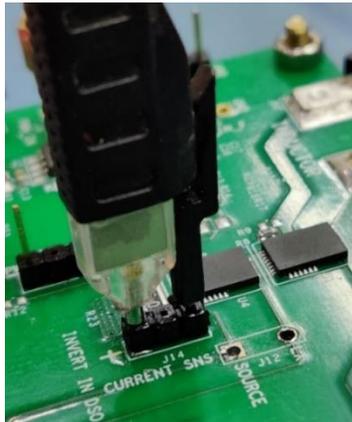


Figure 3-3: Active probe connection for observing Drain-Source Current through current sense

The current value in Ampere will be ten times (10X) that of the voltage measured in Volts since the current sense resistor is 0.1Ω. For example, 100 mV across the current sense resistor corresponds to 1 A Drain-Source current.

4 Key Switching Waveforms Observed From DSO

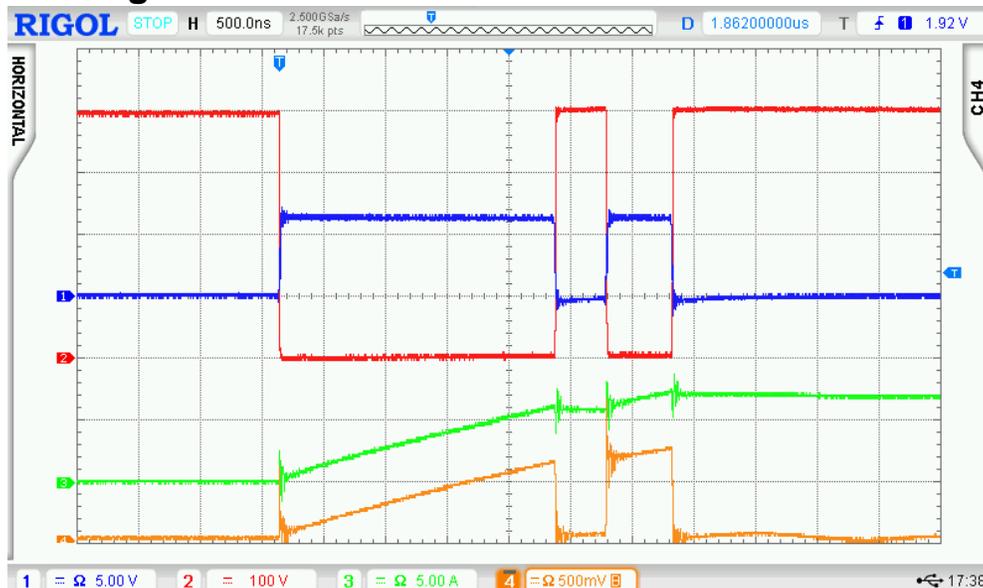


Figure 4-1: Typical Double Pulse Test Waveform captured using DSO. Channel 1(Blue): PWM input (5 V/div); Channel 2(Red): Drain-Source voltage (100 V/div); Channel 3(Green): Inductor Current (5 A/div); Channel 4(Orange): Voltage across 0.1 Ω current sense resistor (500 mV/div); Time scale: 500ns/div

5 Schematic Diagram

The electrical schematic diagram of the EVB is shown in Figure 5-1. Various circuit blocks are identified on this diagram to help the user identify or debug the EVB.

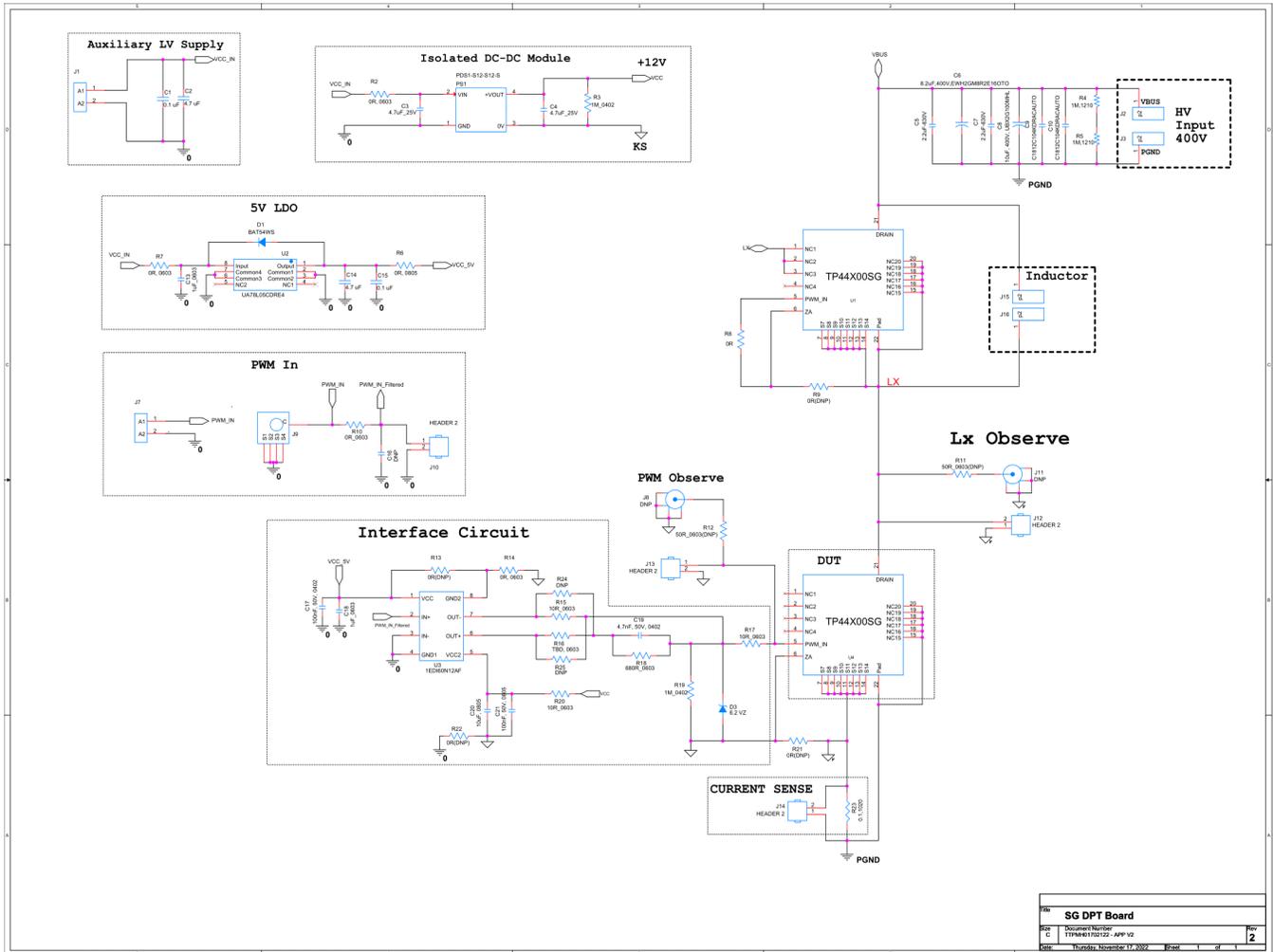


Figure 5-1: Schematic diagram of TP44200SG-DPT-EVB Eval Board.

6 Board Layout

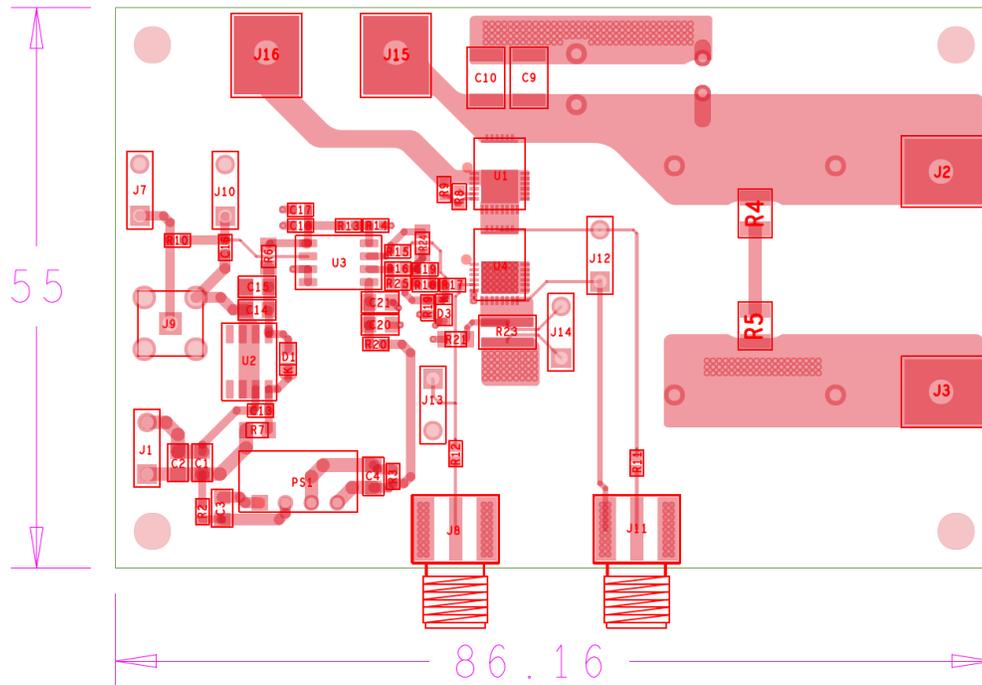


Figure 6-1: EVB PCB Layout of the Top Layer.

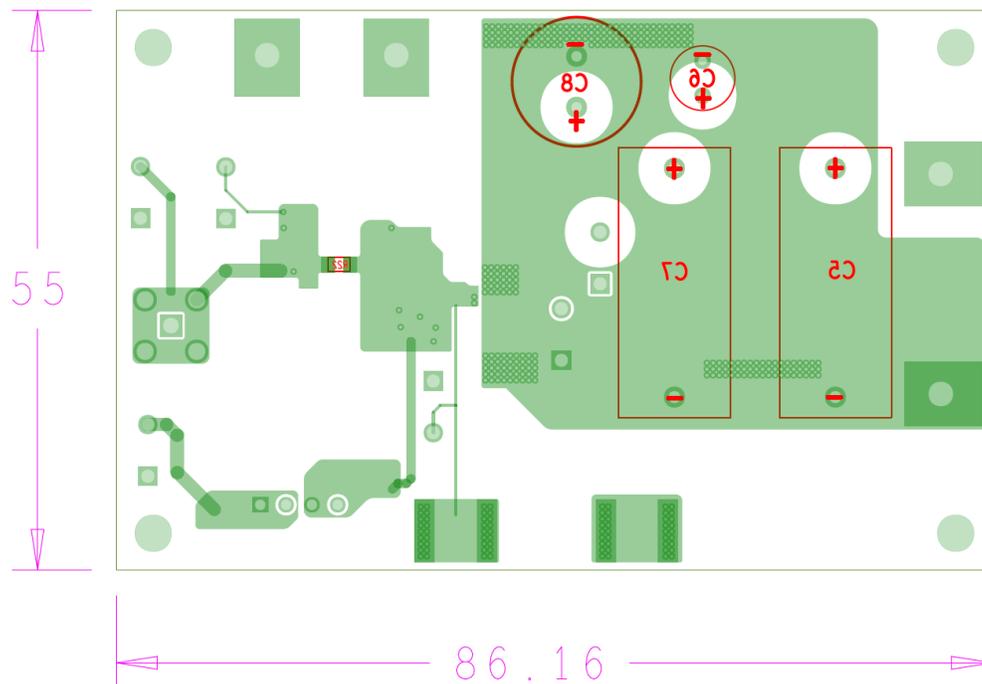


Figure 6-2: EVB PCB Layout of the Bottom Layer.

7 Bill Of Materials

Table 7-1: Bill of Materials (BOM) for TP44200SG-DPT-EVB

TP44200SG-DPT-EVB; BOM Version: 1.1						
Sl. #	Qty.	Ref. Des.	Part Description	Manufacturer	Manufacturer P/N	Package
1	1	C1	DNP			
2	1	C15	DNP			
3	1	C2	4.7 uF, 25 V, X7R, 0603	Standard	Standard	0603
4	1	C14	4.7 uF, 25 V, X7R, 0603	Standard	Standard	0603
5	1	C3	4.7 uF, 25 V, X7R, 0603	Standard	Standard	0603
6	1	C4	4.7 uF, 25 V, X7R, 0603	Standard	Standard	0603
7	1	C5	DNP			
8	1	C7	DNP			
9	1	C6	DNP			
10	1	C8	27 uF, 400 V,	Standard	Standard	TH
11	1	C9	100 nF, 630 V, X7R, 10%	KEMET	C1812C104KDRACAUT O	1812
12	1	C10	100 nF, 630 V, X7R, 10%	KEMET	C1812C104KDRACAUT O	1812
13	1	C13	1 uF, 25 V, X7R, 0603	Standard	Standard	0603
14	1	C18	1 uF, 25 V, X7R, 0603	Standard	Standard	0603
15	1	C16	DNP			0603
16	1	C17	DNP			0603
17	1	C19	4.7 nF, 25 V, X7R, 0603	Standard	Standard	0603
18	1	C20	4.7 uF, 25 V, X7R, 0805	Standard	Standard	0805
19	1	C21	100 nF, 25 V, X7R, 0805	Standard	Standard	0805
20	1	D1	DIODE SCHOTTKY 30 V 200 mA SOD323	Standard	BAT54WS	SOD-323
21	1	D3	DIODE ZENER 6.2 V 300 mW SOD323	Onsemi	SZMM3Z6V2ST1G	SOD-323
22	1	J1	HEADER 2 Pin	Standard	Standard	TH
23	1	J7	HEADER 2 Pin	Standard	Standard	TH
24	1	J2	Banana Jack Red 4mm	Standard	Standard	
25	1	J15	Banana Jack Red 4mm	Standard	Standard	
26	1	J3	Banana Jack Black 4mm	Standard	Standard	
27	1	J16	Banana Jack Black 4mm	Standard	Standard	
28	1	J8	DNP			
29	1	J11	DNP			
30	1	J9	SMA Connector	Standard	Standard	TH
31	1	J10	DNP			
32	1	J12	DNP			
33	1	J13	HEADER 2 Pin	Standard	Standard	TH
34	1	J14	HEADER 2 Pin	Standard	Standard	TH
35	1	PS1	Isolated DC-DC Converter	CUI Inc.	PDS1-S12-S12-S	TH
36	1	R2	RES 0 OHM JUMPER 1/10W 0603	Standard	Standard	0603
37	1	R3	RES 1 MOHM 5% 1/10 W 0603	Standard	Standard	0603
38	1	R19	RES 1 MOHM 5% 1/10 W 0603	Standard	Standard	0603
39	1	R4	RES 1 MOHM 5% ½ W 1210	Standard	Standard	1210
40	1	R5	RES 1 MOHM 5% ½ W 1210	Standard	Standard	1210
41	1	R6	RES 0 OHM JUMPER 1/8 W 0805	Standard	Standard	0805
42	1	R7	RES 0 OHM JUMPER 1/10 W 0603	Standard	Standard	0603
43	1	R8	RES 0 OHM JUMPER 1/10 W 0603	Standard	Standard	0603
44	1	R9	DNP			
45	1	R13	DNP			
46	1	R10	RES 0 OHM JUMPER 1/10 W 0603	Standard	Standard	0603
47	1	R11	DNP			
48	1	R12	DNP			
49	1	R14	RES 0 OHM JUMPER 1/10 W 0603	Standard	Standard	0603
50	1	R15	RES 5 OHM 1% 1/10 W 0603	Standard	Standard	0603
51	1	R17	RES 5 OHM 1% 1/10 W 0603	Standard	Standard	0603
52	1	R20	RES 10 OHM 1% 1/10 W 0603	Standard	Standard	0603
53	1	R16	RES 20 OHM 1% 1/10 W 0603	Standard	Standard	0603
54	1	R18	RES 680 OHM 1% 1/10 W 0603	Standard	Standard	0603
55	1	R21	DNP			

TP44200SG-DPT-EVB; BOM Version: 1.1						
Sl. #	Qty.	Ref. Des.	Part Description	Manufacturer	Manufacturer P/N	Package
56	1	R22	DNP			
57	1	R23	RES 0.100 OHM 1% 1 W 2010	Standard	Standard	1020
58	1	R24	DNP			
59	1	R25	DNP			
60	1	U1	GaN E-HEMT	Tagore Technology	TP44200SG	QFN 5X7
61	1	U4	GaN E-HEMT	Tagore Technology	TP44200SG	QFN 5X7
62	1	U2	LDO 5V, 100mA	Texas Instruments	UA78L05CDRE4	SOIC-8
63	1	U3	Gate Drivers 1200V Isolated 1-CH, 9.4 A	Infineon Tech.	1EDI60N12AF	DSO-8
64	1		EVB PCB	Tagore Technology	TTPMH01702122-APP V2	

Revision History

Document version	Date of release	Description of changes
Rev 1.0	25-Nov-2022	First release
Rev 1.1	25-Sep-2023	Revised: EVB Name, Table 2-1, BOM. Font changed.